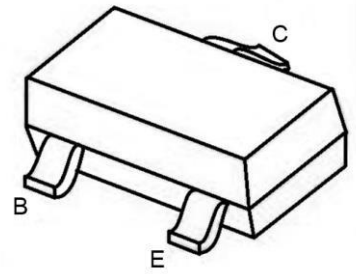
GPB8550 Transistor(PNP)

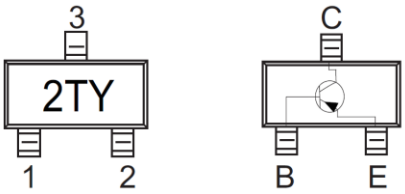
SOT-23



Feature

- Good Current Characters
- Small Saturable Voltage Drop
- High Breakdown Voltage

Marking:



Classification of h_{FE}:

Rank	L	H	J
Range	120-200	200-350	300-400

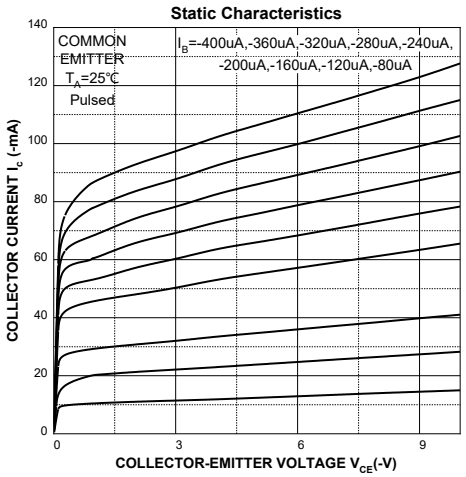
MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

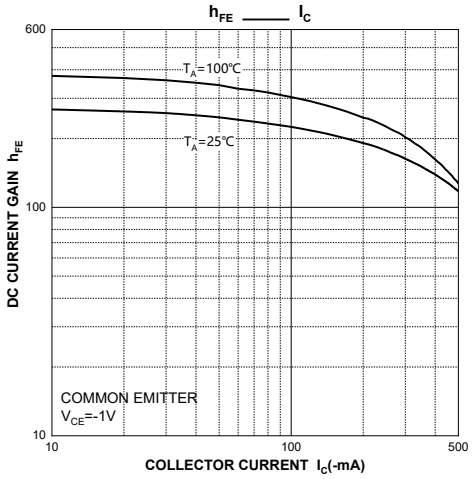
Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	-0.5	A
Power Dissipation	P_d	300	mW
Junction Temperature	T_J	-55~ +150	℃
Storage Temperature	T_{STG}	-55~ +150	℃

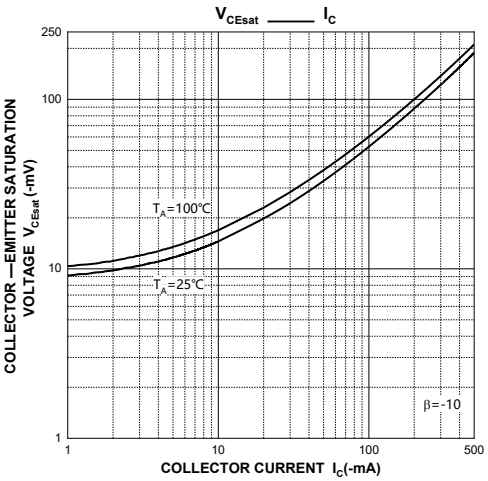
ELECTRICAL CHARACTERISTICS(T_A=25℃ unless otherwise noted)

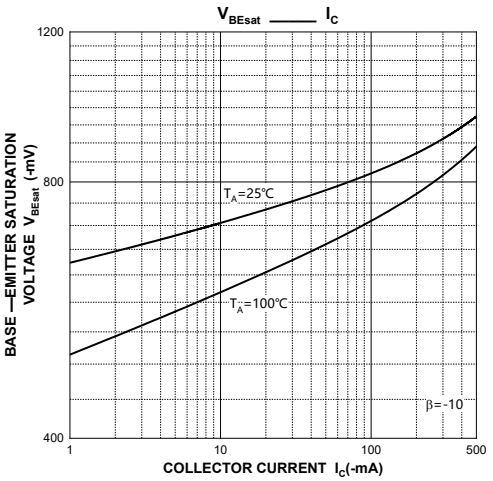
Parameter	Symbol	Test Condition	Min	Max	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C = -100μA ,I_E = 0	-40		V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = -1mA , I_B = 0	-25		V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E = -100μA,I_C = 0	-5		V
Collector Cut-off Current	I_{CBO}	V_{CB} = -40V, I_E = 0		-100	nA
Emitter Cut-off Current	I_{EBO}	V_{EB} = -3V, I_C = 0		-100	nA
DC Current Gain	h_{FE}	V_{CE} = -1V, I_C = -0.1mA	40		
		V_{CE} = -1V, I_C = -1mA	70		
		V_{CE} = -1V, I_C = -50mA	120	400	
		V_{CE} = -1V, I_C = -100mA	60		
		V_{CE} = -1V, I_C = -500mA	50		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = -100mA, I_B = -10mA		-0.5	V
		I_C = -500mA, I_B = -50mA		-0.6	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C = -100mA, I_B = -10mA		-1.1	V
		I_C = -500mA, I_B = -50mA		-1.2	V
Transition Frequency	f_T	V_{CE} = -6V, I_C = -20mA,f = 30MHz	150		MHZ

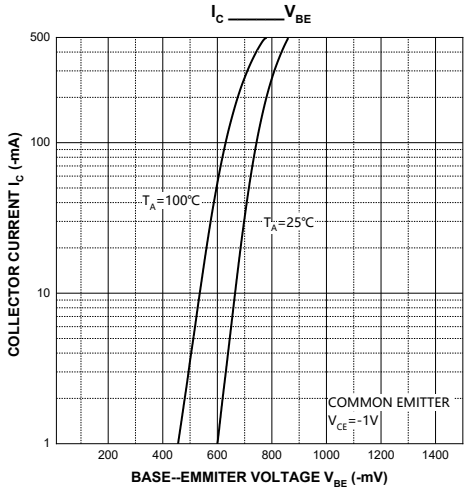
Typical Characteristics

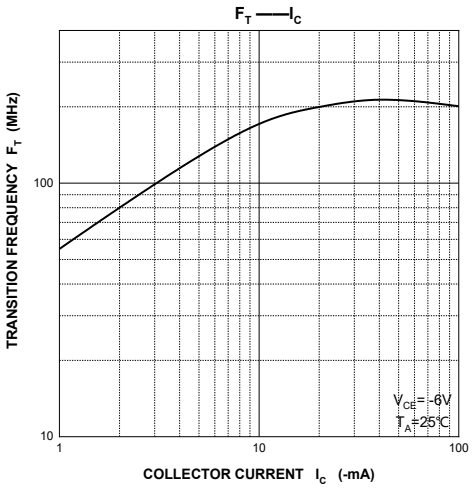


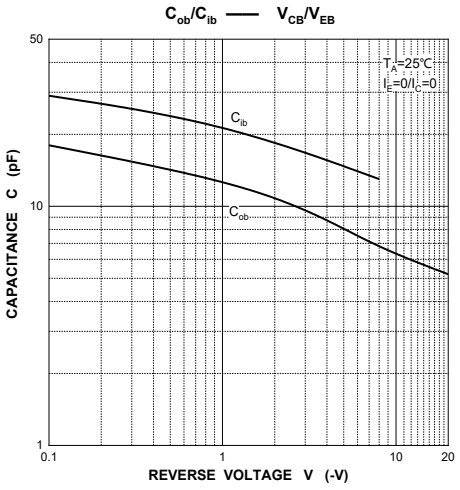


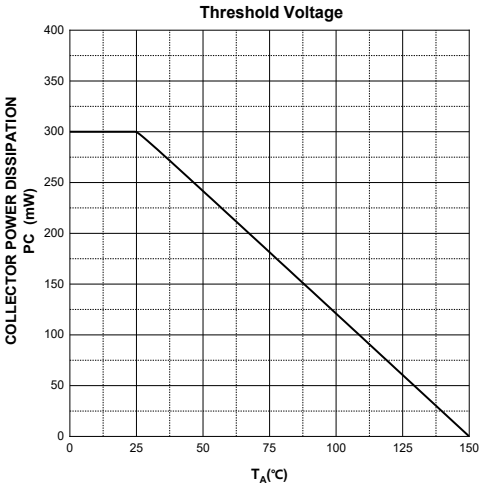




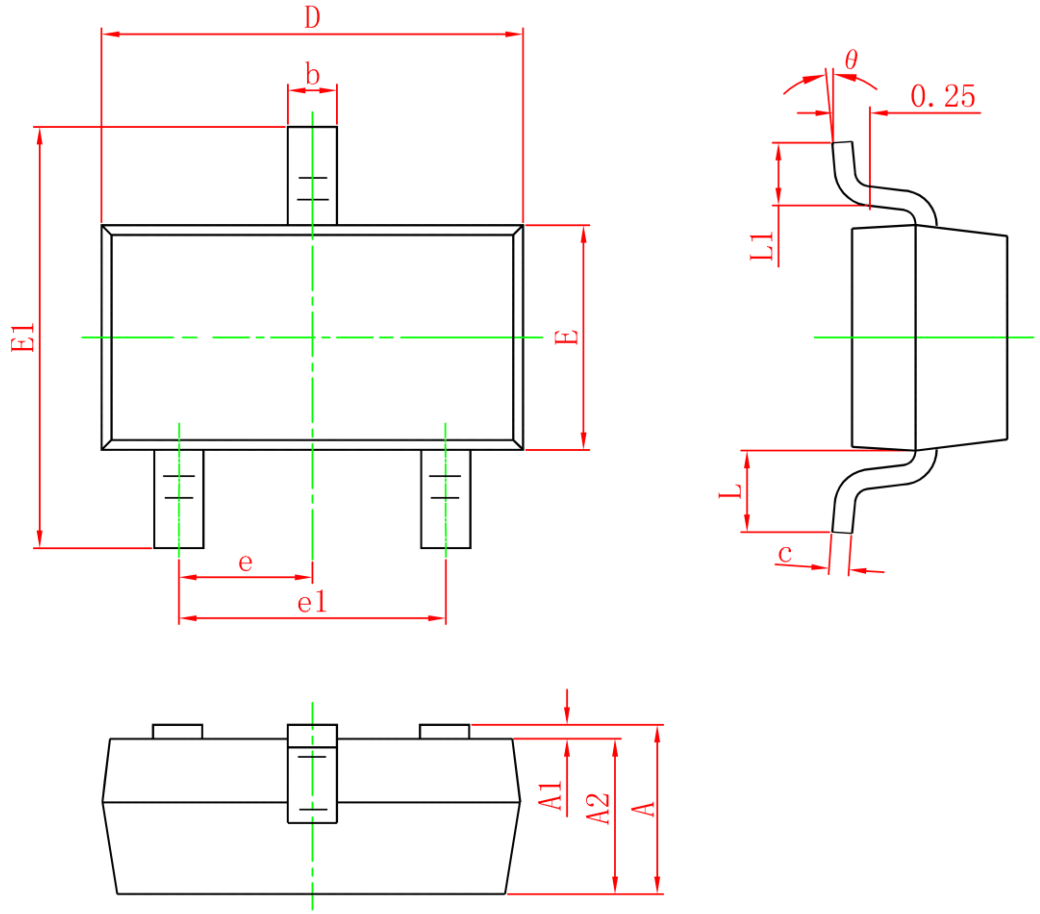





C_{ob}/C_{ib} —— V_{CB}/V_{EB}
T_A=25℃
I_E=0/I_C=0
C_{ib}
C_{ob}
CAPACITANCE C (pF)
50
10
1
0.1
1
10
20
REVERSE VOLTAGE V (-V)


Threshold Voltage
COLLECTOR POWER DISSIPATION
PC (mW)
400
350
300
250
200
150
100
50
0
0
25
50
75
100
125
150
T_A(℃)

SOT-23 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0	0.100	0	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.150	1.500	0.045	0.059
E1	2.250	2.650	0.089	0.104
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

Attention：

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